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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Active
Core Processor	e200z7
Core Size	32-Bit Tri-Core
Speed	264MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexCANbus, LINbus, SCI, SPI
Peripherals	DMA, LVD, POR, Zipwire
Number of I/O	-
Program Memory Size	8MB (8M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 16b Sigma-Delta, eQADC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	416-BGA
Supplier Device Package	416-MAPBGA (27x27)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5777csk3mme3">https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5777csk3mme3</a>

Pinouts

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	
A	VSS	VDD	RSTOUT	ANAO_SDA0					VDDA_SD	REFBYPCA25	VRL_SD	VRH_SD	AN28	AN32	AN36	VDDA_EQ	REFBYPCB25	VRL_EQ	VRH_EQ	ANB7_SDD7	ANB11	ANB14	ANB17	ANB21	ANB23	VSS	A
B	VDDEH1	VSS	VDD	TEST	ANA1_SDA1	ANA5	ANA10	ANA14	VDDA_MISO	VSSA_SD	REFBYPCA75	AN24	AN27	AN29	AN33	VDDA_EQ	VSSA_EQ	REFBYPCB75	ANB6_SDD6	ANB8	ANB10	ANB15	ANB18	ANB22	VSS	TCRCLKC	B
C	ETPUA30	ETPUA31	VSS	VDD	ANA2_SDA2	ANA6	ANA9	ANA13	ANA17_SDB1	ANA19_SDB3	ANA21_SDC1	ANA23_SDC3	AN26	AN30	AN34	AN37	AN38	ANB0_SDD0	ANB4_SDD4	ANB5_SDD5	ANB12	ANB16	ANB19	VSS	ETPUC0	ETPUC1	C
D	ETPUA27	ETPUA28	ETPUA29	VSS	VDD	ANA3_SDA3	ANA7	ANA12	ANA16_SDB0	ANA18_SDB2	ANA20_SDC0	ANA22_SDC2	AN25	AN31	AN35	AN39	ANB1_SDD1	ANB2_SDD2	ANB3_SDD3	ANB9	ANB13	ANB20	VSS	SEN72_A	ETPUC2	ETPUC3	D
E	ETPUA23	ETPUA24	ETPUA25	ETPUA26																			VDDEH7	ETPUC4	ETPUC5	ETPUC6	E
F	ETPUA19	ETPUA20	ETPUA21	ETPUA22																			ETPUC7	ETPUC8	ETPUC9	ETPUC10	F
G	ETPUA15	ETPUA16	ETPUA17	ETPUA18																			ETPUC11	ETPUC12	ETPUC13	ETPUC14	G
H	ETPUA11	ETPUA12	ETPUA14	ETPUA13																			ETPUC15	ETPUC16	ETPUC17	ETPUC18	H
J	ETPUA7	ETPUA8	ETPUA9	ETPUA10																			ETPUC19	ETPUC20	ETPUC21	ETPUC22	J
K	ETPUA3	ETPUA4	ETPUA5	ETPUA6																			ETPUC23	ETPUC24	ETPUC25	ETPUC26	K
L	TCRCLKA	ETPUA0	ETPUA1	ETPUA2																			ETPUC27	ETPUC28	ETPUC29	ETPUC30	L
M	NC	TXDA	RXDA	VSTBY																			ETPUC31	ETPU815	ETPU814	VDDEH7	M
N	RXDB	BOOTCFG1	WKPCFG	VDD																			VDDEH6	ETPU811	ETPU812	ETPU813	N
P	TXDB	PLLCFG1	PLLCFG2	VDDEH1																			ETPU87	ETPU88	ETPU89	ETPU810	P
R	JCOMP	RESET	PLLCFG0	RDY																			ETPU83	ETPU84	ETPU85	ETPU86	R
T	VDDE2	MCKO	MSE01	EVTI																			TCRCLKB	ETPU80	ETPU81	ETPU82	T
U	EVT0	MSE00	MDO0	MDO1																			ETPU819	ETPU818	ETPU817	ETPU816	U
V	MDO2	MDO3	MDO4	MDO5																			ETPU826	ETPU822	ETPU821	ETPU820	V
W	MDO6	MDO7	MDO8	VDDE2																			REGSEL	ETPU825	ETPU824	ETPU823	W
Y	MDO9	MDO10	MDO11	MDO15																			ETPU829	ETPU828	ETPU827	REGCTL	Y
AA	MDO12	MDO13	MDO14	NC																			VDDEH5	ETPU830	VDDEH4	VSS5VW	AA
AB	TDO	TCK	TMS	VDD																			VDD	ETPU831	VSSPW	EXTAL	AB
AC	VDDE2	TDI	VDD	VSS	FEC_TXCLKREFCLK	PCSA1	PCSA2	PCSA4	PCSB1	VDDEH3	VDDEH4	VDD	EMIOS8	EMIOS14	EMIOS18	EMIOS22	EMIOS27	EMIOS31	CNRX8	CNRXD	VDDEH5	PCSC1	VSSPMC	VDD	VDDEH6	XTAL	AC
AD	ENGCLK	VDD	VSS	FEC_TXD0	FEC_TXD1	PCSA5	SOUTA	SCKA	PCSB0	PCSB3	EMIOS2	EMIOS5	EMIOS9	EMIOS15	EMIOS19	EMIOS23	EMIOS26	EMIOS30	CNTX8	CNTXD	SCKC	RXDC	PCSC3	VSS	VDD	VDDFLA	AD
AE	VDD	VSS	FEC_RX_DV	FEC_TX_EN	PCSA4	PCSA0	PCSA3	SCKB	SINB	EMIOS0	EMIOS3	EMIOS6	EMIOS10	EMIOS13	EMIOS17	EMIOS21	EMIOS25	EMIOS29	CNRXA	CNRXC	PCSC0	SINC	PCSC2	PCSC5	VSS	VDD	AE
AF	VSS	VDDE2A	FEC_RXD0	FEC_RXD1	VDDEH3A	PCSB5	SINA	PCSB2	SOUTB	EMIOS1	EMIOS4	EMIOS7	EMIOS11	EMIOS12	EMIOS16	EMIOS20	EMIOS24	EMIOS28	CNTXA	CNTXC	SOUTC	VDDEH4	TXDC	PCSC4	VDDEH5	VSS	AF
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	

Figure 2. MPC5777C 416-ball MAPBGA (full diagram)

2.2 516-ball MAPBGA pin assignments

Figure 3 shows the 516-ball MAPBGA pin assignments.



The following information includes details about power considerations, DC/AC electrical characteristics, and AC timing specifications.

Absolute maximum specifications are stress ratings only. Functional operation at these maxima is not guaranteed.

Stress beyond listed maxima may affect device reliability or cause permanent damage to the device.

**Table 9. GPIO and EBI data pad output buffer electrical characteristics (SR pads)<sup>1</sup>**  
(continued)

Symbol	Parameter	Conditions <sup>2</sup>		Value <sup>3</sup>			Unit
				Min	Typ	Max	
$t_{R\_F}$	GPIO pad output transition time (rise/fall)	PCR[SRC] = 11b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 25 pF	—	—	1.2	ns
			$C_L$ = 50 pF	—	—	2.5	
			$C_L$ = 200 pF	—	—	8	
		PCR[SRC] = 11b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 25 pF	—	—	1.7	
			$C_L$ = 50 pF	—	—	3.25	
			$C_L$ = 200 pF	—	—	12	
		PCR[SRC] = 10b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	5	
			$C_L$ = 200 pF	—	—	18	
		PCR[SRC] = 10b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 50 pF	—	—	7	
			$C_L$ = 200 pF	—	—	25	
		PCR[SRC] = 01b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	13	
			$C_L$ = 200 pF	—	—	24	
		PCR[SRC] = 01b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 50 pF	—	—	25	
			$C_L$ = 200 pF	—	—	30	
		PCR[SRC] = 00b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	24	
			$C_L$ = 200 pF	—	—	50	
		PCR[SRC] = 00b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 50 pF	—	—	40	
			$C_L$ = 200 pF	—	—	51	
$t_{PD}$	GPIO pad output propagation delay time	PCR[SRC] = 11b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	6	ns
			$C_L$ = 200 pF	—	—	13	
		PCR[SRC] = 11b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 50 pF	—	—	8.25	
			$C_L$ = 200 pF	—	—	19.5	
		PCR[SRC] = 10b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	9	
			$C_L$ = 200 pF	—	—	22	
		PCR[SRC] = 10b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 50 pF	—	—	12.5	
			$C_L$ = 200 pF	—	—	35	
		PCR[SRC] = 01b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	27	
			$C_L$ = 200 pF	—	—	40	
		PCR[SRC] = 01b 3.0 V < $V_{DDEX}$ < 3.6 V	$C_L$ = 50 pF	—	—	45	
			$C_L$ = 200 pF	—	—	65	
		PCR[SRC] = 00b 4.5 V < $V_{DDEX}$ < 5.5 V	$C_L$ = 50 pF	—	—	40	
			$C_L$ = 200 pF	—	—	65	
$ t_{SKEW\_W} $	Difference between rise and fall time	—	PCR[SRC] = 00b 3.0 V < $V_{DDEX}$ < 3.6 V	—	—	75	%
			$C_L$ = 200 pF	—	—	100	

1. All GPIO pad output specifications are valid for 3.0 V <  $V_{DDEX}$  < 5.5 V, except where explicitly stated.

## Electrical characteristics

- PCR[Src] values refer to the setting of that register field in the SIU.
- All values to be confirmed during device validation.

The following table shows the EBI CLKOUT, address, and control signal pad electrical characteristics. These pads can also be used for GPIO.

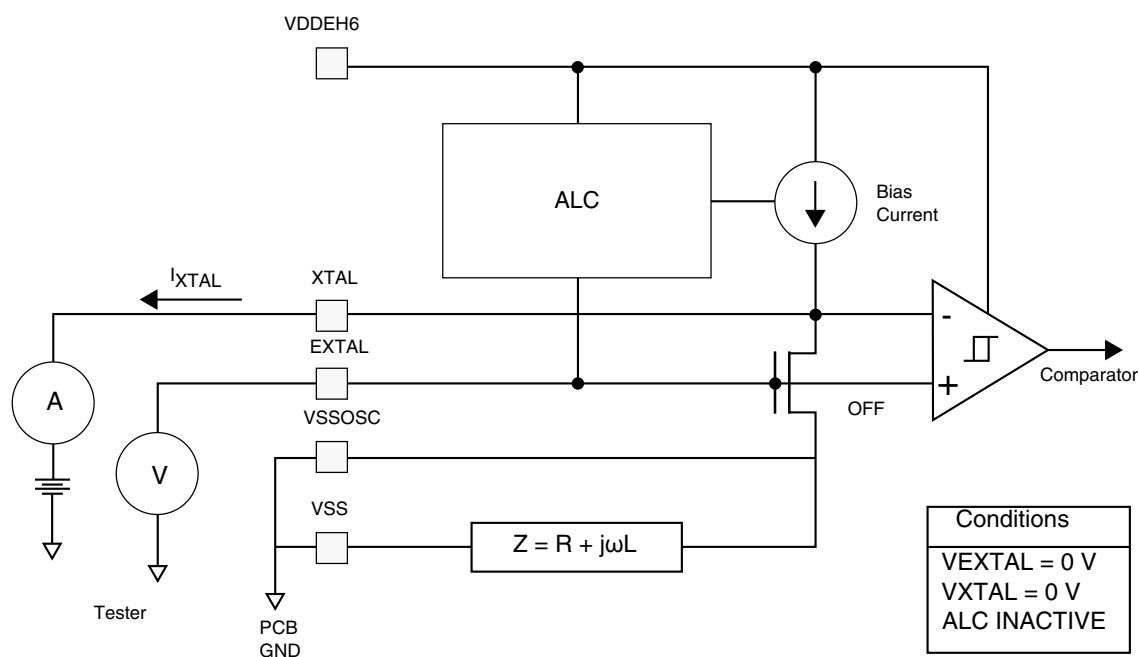
**Table 10. GPIO and EBI CLKOUT, address, and control signal pad output buffer electrical characteristics (FC pads)**

Symbol	Parameter	Conditions <sup>1</sup>	Value			Unit	
			Min	Typ	Max		
EBI Mode Output Specifications: valid for 3.0 V < V <sub>DDEx</sub> < 3.6 V							
C <sub>DRV</sub>	External bus load capacitance	PCR[DSC] = 01b	—	—	10	pF	
		PCR[DSC] = 10b	—	—	20		
		PCR[DSC] = 11b	—	—	30		
f <sub>MAX_EBI</sub>	External bus maximum operating frequency	C <sub>DRV</sub> = 10/20/30 pF	—	—	66	MHz	
GPIO and EBI Mode Output Specifications							
I <sub>OH_EBI</sub>	GPIO and external bus pad output high current	V <sub>OH</sub> = 0.8 * V <sub>DDEx</sub> 4.5 V < V <sub>DDEx</sub> < 5.5 V	PCR[DSC] = 11b	30	—	—	mA
			PCR[DSC] = 10b	22	—	—	
			PCR[DSC] = 01b	13	—	—	
			PCR[DSC] = 00b	2	—	—	
		V <sub>OH</sub> = 0.8 * V <sub>DDEx</sub> 3.0 V < V <sub>DDEx</sub> < 3.6 V	PCR[DSC] = 11b	16	—	—	
			PCR[DSC] = 10b	12	—	—	
			PCR[DSC] = 01b	7	—	—	
			PCR[DSC] = 00b	1	—	—	
I <sub>OL_EBI</sub>	GPIO and external bus pad output low current	V <sub>OL</sub> = 0.2 * V <sub>DDEx</sub> 4.5 V < V <sub>DDEx</sub> < 5.5 V	PCR[DSC] = 11b	54	—	—	mA
			PCR[DSC] = 10b	25	—	—	
			PCR[DSC] = 01b	16	—	—	
			PCR[DSC] = 00b	2	—	—	
		V <sub>OL</sub> = 0.2 * V <sub>DDEx</sub> 3.0 V < V <sub>DDEx</sub> < 3.6 V	PCR[DSC] = 11b	17	—	—	
			PCR[DSC] = 10b	14	—	—	
			PCR[DSC] = 01b	8	—	—	
			PCR[DSC] = 00b	1	—	—	
t <sub>R_F_EBI</sub>	GPIO and external bus pad output transition time (rise/fall)	PCR[DSC] = 11b	C <sub>L</sub> = 30 pF	—	—	1.5	ns
			C <sub>L</sub> = 50 pF	—	—	2.4	
		PCR[DSC] = 10b	C <sub>L</sub> = 20 pF	—	—	1.5	
		PCR[DSC] = 01b	C <sub>L</sub> = 10 pF	—	—	1.85	
		PCR[DSC] = 00b	C <sub>L</sub> = 50 pF	—	—	45	
t <sub>PD_EBI</sub>	GPIO and external bus pad output propagation delay time	PCR[DSC] = 11b	C <sub>L</sub> = 30 pF	—	—	4.2	ns
			C <sub>L</sub> = 50 pF	—	—	5.5	
		PCR[DSC] = 10b	C <sub>L</sub> = 20 pF	—	—	4.2	
		PCR[DSC] = 01b	C <sub>L</sub> = 10 pF	—	—	4.4	
		PCR[DSC] = 00b	C <sub>L</sub> = 50 pF	—	—	59	

**Table 15. Selectable load capacitance (continued)**

load_cap_sel[4:0] from DCF record	Load capacitance <sup>1, 2</sup> (pF)
01110	14.9
01111	15.8

1. Values are determined from simulation across process corners and voltage and temperature variation. Capacitance values vary  $\pm 12\%$  across process,  $0.25\%$  across voltage, and no variation across temperature.
2. Values in this table do not include the die and package capacitances given by  $C_{S\_XTAL}/C_{S\_EXTAL}$  in Table 14.



### Figure 7. Test circuit

### Table 16. Internal RC (IRC) oscillator electrical specifications

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
$f_{\text{Target}}$	IRC target frequency	—	—	16	—	MHz
$\delta f_{\text{var\_T}}$	IRC frequency variation	T < 150 °C	−8	—	8	%

### 3.8 Analog-to-Digital Converter (ADC) electrical specifications

5. Below disruptive current conditions, the channel being stressed has conversion values of \$3FF for analog inputs greater than  $V_{RH}$  and \$000 for values less than  $V_{RL}$ . Other channels are not affected by non-disruptive conditions.
6. Exceeding limit may cause conversion error on stressed channels and on unstressed channels. Transitions within the limit do not affect device reliability or cause permanent damage.
7. Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values using  $V_{POSCLAMP} = V_{DDA} + 0.5 \text{ V}$  and  $V_{NEGCLAMP} = -0.3 \text{ V}$ , then use the larger of the calculated values.
8. Condition applies to two adjacent pins at injection limits.
9. Performance expected with production silicon.
10. All channels have same  $10 \text{ k}\Omega < R_s < 100 \text{ k}\Omega$ . Channel under test has  $R_s = 10 \text{ k}\Omega$ ,  $I_{INJ} = I_{INJMAX}, I_{INJMIN}$ .
11. The TUE specification is always less than the sum of the INL, DNL, offset, and gain errors due to cancelling errors.
12. TUE does not apply to differential conversions.
13. Variable gain is controlled by setting the PRE\_GAIN bits in the ADC\_ACR1-8 registers to select a gain factor of  $\times 1$ ,  $\times 2$ , or  $\times 4$ . Settings are for differential input only. Tested at  $\times 1$  gain. Values for other settings are guaranteed as indicated.
14. Guaranteed 10-bit monotonicity.
15. At  $V_{RH\_EQ} - V_{RL\_EQ} = 5.12 \text{ V}$ , one LSB = 1.25 mV.

### 3.8.2 Sigma-Delta ADC (SDADC)

The SDADC is a 16-bit Sigma-Delta analog-to-digital converter with a 333 Ksps maximum output conversion rate.

#### NOTE

The voltage range is 4.5 V to 5.5 V for SDADC specifications, except where noted otherwise.

**Table 18. SDADC electrical specifications**

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
V <sub>IN</sub>	ADC input signal	—	0	—	V <sub>DDA_SD</sub>	V
V <sub>IN_PK2PK</sub> <sup>1</sup>	Input range peak to peak  V <sub>IN_PK2PK</sub> = V <sub>INP</sub> <sup>2</sup> – V <sub>INM</sub> <sup>3</sup>	Single ended V <sub>INM</sub> = V <sub>RL_SD</sub>	V <sub>RH_SD</sub> /GAIN			V
		Single ended V <sub>INM</sub> = 0.5*V <sub>RH_SD</sub> GAIN = 1	±0.5*V <sub>RH_SD</sub>			
		Single ended V <sub>INM</sub> = 0.5*V <sub>RH_SD</sub> GAIN = 2,4,8,16	±V <sub>RH_SD</sub> /GAIN			
		Differential 0 < V <sub>IN</sub> < V <sub>DDEx</sub>	±V <sub>RH_SD</sub> /GAIN			
f <sub>ADCD_M</sub>	SD clock frequency <sup>4</sup>	—	4	14.4	16	MHz
f <sub>ADCD_S</sub>	Conversion rate	—	—	—	333	Ksps
—	Oversampling ratio	Internal modulator	24	—	256	—
RESOLUTION	SD register resolution <sup>5</sup>	2's complement notation	16			bit

Table continues on the next page...

Table 18. SDADC electrical specifications (continued)

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
GAIN	ADC gain	Defined through SDADC_MCR[PGAN]. Only integer powers of 2 are valid gain values.	1	—	16	—
$\delta_{\text{GAIN}}$	Absolute value of the ADC gain error <sup>6, 7</sup>	Before calibration (applies to gain setting = 1)	—	—	1.5	%
		After calibration $\Delta V_{\text{RH\_SD}} < 5\%$ , $\Delta V_{\text{DDA\_SD}} < 10\%$ $\Delta T_{\text{J}} < 50\text{ }^{\circ}\text{C}$	—	—	5	mV
		After calibration $\Delta V_{\text{RH\_SD}} < 5\%$ , $\Delta V_{\text{DDA\_SD}} < 10\%$ $\Delta T_{\text{J}} < 100\text{ }^{\circ}\text{C}$	—	—	7.5	
		After calibration $\Delta V_{\text{RH\_SD}} < 5\%$ , $\Delta V_{\text{DDA\_SD}} < 10\%$ $\Delta T_{\text{J}} < 150\text{ }^{\circ}\text{C}$	—	—	10	
$V_{\text{OFFSET}}$	Conversion offset <sup>6, 7</sup>	Before calibration (applies to all gain settings: 1, 2, 4, 8, 16)	—	$10 \cdot (1 + 1/\text{gain})$	20	mV
		After calibration $\Delta V_{\text{DDA\_SD}} < 10\%$ $\Delta T_{\text{J}} < 50\text{ }^{\circ}\text{C}$	—	—	5	
		After calibration $\Delta V_{\text{DDA\_SD}} < 10\%$ $\Delta T_{\text{J}} < 100\text{ }^{\circ}\text{C}$	—	—	7.5	
		After calibration $\Delta V_{\text{DDA\_SD}} < 10\%$ $\Delta T_{\text{J}} < 150\text{ }^{\circ}\text{C}$	—	—	10	

Table continues on the next page...



**Table 18. SDADC electrical specifications (continued)**

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
SNR <sub>SE150</sub>	Signal to noise ratio in single ended mode, 150 Ksps output rate	4.5 V < V <sub>DDA_SD</sub> < 5.5 V <sup>8,9</sup> V <sub>RH_SD</sub> = V <sub>DDA_SD</sub> GAIN = 1	72	—	—	dB
		4.5 V < V <sub>DDA_SD</sub> < 5.5 V <sup>8,9</sup> V <sub>RH_SD</sub> = V <sub>DDA_SD</sub> GAIN = 2	69	—	—	
		4.5 V < V <sub>DDA_SD</sub> < 5.5 V <sup>8,9</sup> V <sub>RH_SD</sub> = V <sub>DDA_SD</sub> GAIN = 4	66	—	—	
		4.5 V < V <sub>DDA_SD</sub> < 5.5 V <sup>8,9</sup> V <sub>RH_SD</sub> = V <sub>DDA_SD</sub> GAIN = 8	62	—	—	
		4.5 V < V <sub>DDA_SD</sub> < 5.5 V <sup>8,9</sup> V <sub>RH_SD</sub> = V <sub>DDA_SD</sub> GAIN = 16	54	—	—	
SINAD <sub>DIFF150</sub>	Signal to noise and distortion ratio in differential mode, 150 Ksps output rate	Gain = 1 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	72	—	—	dBFS
		Gain = 2 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	72	—	—	
		Gain = 4 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	69	—	—	
		Gain = 8 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	68.8	—	—	
		Gain = 16 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	64.8	—	—	

Table continues on the next page...

**Table 18. SDADC electrical specifications (continued)**

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
THD <sub>DIFF150</sub>	Total harmonic distortion in differential mode, 150 Ksps output rate	Gain = 1 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	65	—	—	dBFS
		Gain = 2 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	68	—	—	
		Gain = 4 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	74	—	—	
		Gain = 8 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	80	—	—	
		Gain = 16 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	80	—	—	
THD <sub>DIFF333</sub>	Total harmonic distortion in differential mode, 333 Ksps output rate	Gain = 1 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	65	—	—	dBFS
		Gain = 2 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	68	—	—	
		Gain = 4 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	74	—	—	
		Gain = 8 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	80	—	—	
		Gain = 16 4.5 V < V <sub>DDA_SD</sub> < 5.5 V V <sub>RH_SD</sub> = V <sub>DDA_SD</sub>	80	—	—	

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Table 18. SDADC electrical specifications (continued)

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
$t_{\text{SETTLING}}$	Settling time after mux change	Analog inputs are muxed HPF = ON	—	—	$2 \cdot \delta_{\text{GROUP}} + 3 \cdot f_{\text{ADCD\_S}}$	—
		HPF = OFF	—	—	$2 \cdot \delta_{\text{GROUP}} + 2 \cdot f_{\text{ADCD\_S}}$	
$t_{\text{ODRECOVERY}}$	Overdrive recovery time	After input comes within range from saturation HPF = ON	—	—	$2 \cdot \delta_{\text{GROUP}} + f_{\text{ADCD\_S}}$	—
		HPF = OFF	—	—	$2 \cdot \delta_{\text{GROUP}}$	
$C_{\text{S\_D}}$	SDADC sampling capacitance after sampling switch <sup>16</sup>	GAIN = 1, 2, 4, 8	—	—	$75 \cdot \text{GAIN}$	fF
		GAIN = 16	—	—	600	fF
$I_{\text{BIAS}}$	Bias consumption	At least one SDADC enabled	—	—	3.5	mA
$I_{\text{ADV\_D}}$	SDADC supply consumption	Per SDADC enabled	—	—	4.325	mA
$I_{\text{ADR\_D}}$	SDADC reference current consumption	Per SDADC enabled	—	—	20	μA

- For input voltage above the maximum and below the clamp voltage of the input pad, there is no latch-up concern, and the signal will only be “clipped.”
- VINP is the input voltage applied to the positive terminal of the SDADC
- VINM is the input voltage applied to the negative terminal of the SDADC
- Sampling is generated internally  $f_{\text{SAMPLING}} = f_{\text{ADCD\_M}}/2$
- For Gain = 16, SDADC resolution is 15 bit.
- Calibration of gain is possible when gain = 1. Offset Calibration should be done with respect to  $0.5 \cdot V_{\text{RH\_SD}}$  for differential mode and single ended mode with negative input =  $0.5 \cdot V_{\text{RH\_SD}}$ . Offset Calibration should be done with respect to 0 for single ended mode with negative input = 0. Both Offset and Gain Calibration is guaranteed for +/-5% variation of  $V_{\text{RH\_SD}}$ , +/-10% variation of  $V_{\text{DDA\_SD}}$ , +/-50 C temperature variation.
- Offset and gain error due to temperature drift can occur in either direction (+/-) for each of the SDADCs on the device.
- SDADC is functional in the range  $3.6 \text{ V} < V_{\text{DDA\_SD}} < 4.0 \text{ V}$ : SNR parameter degrades by 3 dB. SDADC is functional in the range  $3.0 \text{ V} < V_{\text{RH\_SD}} < 4.0 \text{ V}$ : SNR parameter degrades by 9 dB.
- SNR values guaranteed only if external noise on the ADC input pin is attenuated by the required SNR value in the frequency range of  $f_{\text{ADCD\_M}} - f_{\text{ADCD\_S}}$  to  $f_{\text{ADCD\_M}} + f_{\text{ADCD\_S}}$ , where  $f_{\text{ADCD\_M}}$  is the input sampling frequency and  $f_{\text{ADCD\_S}}$  is the output sample frequency. A proper external input filter should be used to remove any interfering signals in this frequency range.
- Input impedance in differential mode  $Z_{\text{IN}} = Z_{\text{DIFF}}$
- Input impedance given at  $f_{\text{ADCD\_M}} = 16 \text{ MHz}$ . Impedance is inversely proportional to SDADC clock frequency.  $Z_{\text{DIFF}} (f_{\text{ADCD\_M}}) = (16 \text{ MHz} / f_{\text{ADCD\_M}}) \cdot Z_{\text{DIFF}}$ ,  $Z_{\text{CM}} (f_{\text{ADCD\_M}}) = (16 \text{ MHz} / f_{\text{ADCD\_M}}) \cdot Z_{\text{CM}}$ .
- Input impedance in single-ended mode  $Z_{\text{IN}} = (2 \cdot Z_{\text{DIFF}} \cdot Z_{\text{CM}}) / (Z_{\text{DIFF}} + Z_{\text{CM}})$
- $V_{\text{INTCM}}$  is the Common Mode input reference voltage for the SDADC. It has a nominal value of  $(V_{\text{RH\_SD}} - V_{\text{RL\_SD}}) / 2$ .
- The ±1% passband ripple specification is equivalent to  $20 \cdot \log_{10} (0.99) = 0.087 \text{ dB}$ .
- Propagation of the information from the pin to the register CDR[CDATA] and the flags SFR[DFF] and SFR[DFFF] is given by the different modules that must be crossed: delta/sigma filters, high pass filter, FIFO module, and clock domain synchronizers. The time elapsed between data availability at the pin and internal SDADC module registers is given by the following formula, where  $f_{\text{ADCD\_S}}$  is the frequency of the sampling clock,  $f_{\text{ADCD\_M}}$  is the frequency of the modulator, and  $f_{\text{FM\_PER\_CLK}}$  is the frequency of the peripheral bridge clock feeds to the SDADC module:

$$\text{REGISTER LATENCY} = t_{\text{LATENCY}} + 0.5/f_{\text{ADCD\_S}} + 2 (\sim+1)/f_{\text{ADCD\_M}} + 2 (\sim+1)f_{\text{FM\_PER\_CLK}}$$

The (~+1) symbol refers to the number of clock cycles uncertainty (from 0 to 1 clock cycle) to be added due to resynchronization of the signal during clock domain crossing.

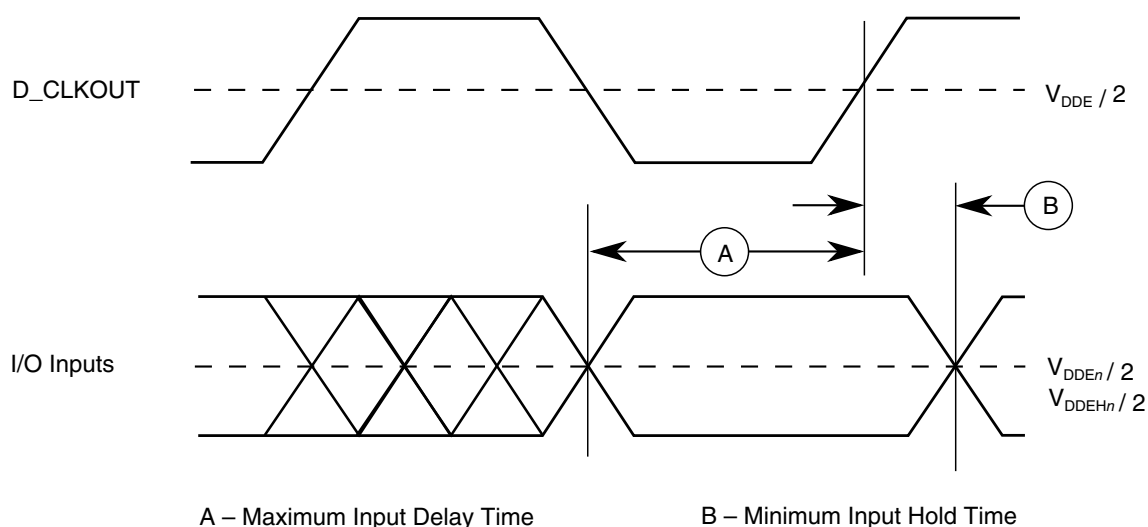
**Table 29. Voltage monitor electrical characteristics<sup>1, 2</sup> (continued)**

Symbol	Parameter	Conditions	Configuration			Value			Unit
			Trim bits	Mask Opt.	Pow. Up	Min	Typ	Max	
POR_HV	HV $V_{DDPMC}$ supply power on reset threshold	Rising voltage (powerup)	N/A	No	Enab.	2444	2600	2756	mV
		Falling voltage (power down)				2424	2580	2736	
LVD_HV	HV internal $V_{DDPMC}$ supply low voltage monitoring	Rising voltage (untrimmed)	4bit	No	Enab.	2935	3023	3112	mV
		Falling voltage (untrimmed)				2922	3010	3099	
		Rising voltage (trimmed)				2946	3010	3066	
		Falling voltage (trimmed)				2934	2998	3044	
HVD_HV	HV internal $V_{DDPMC}$ supply high voltage monitoring	Rising voltage	4bit	Yes	Disab.	5696	5860	5968	mV
		Falling voltage				5666	5830	5938	
LVD_FLASH	FLASH supply low voltage monitoring <sup>6</sup>	Rising voltage (untrimmed)	4bit	No	Enab.	2935	3023	3112	mV
		Falling voltage (untrimmed)				2922	3010	3099	
		Rising voltage (trimmed)				2956	3010	3053	
		Falling voltage (trimmed)				2944	2998	3041	
HVD_FLASH	FLASH supply high voltage monitoring <sup>6</sup>	Rising voltage	4bit	Yes	Disab.	3456	3530	3584	mV
		Falling voltage				3426	3500	3554	
LVD_IO	Main I/O $V_{DDEH1}$ supply low voltage monitoring	Rising voltage (untrimmed)	4bit	No	Enab.	3250	3350	3488	mV
		Falling voltage (untrimmed)				3220	3320	3458	
		Rising voltage (trimmed)				3347	3420	3468	
		Falling voltage (trimmed)				3317	3390	3438	
$t_{VDASSERT}$	Voltage detector threshold crossing assertion	—	—	—	—	0.1	—	2.0	$\mu$ s
$t_{VDRELEASE}$	Voltage detector threshold crossing de-assertion	—	—	—	—	5	—	20	$\mu$ s

1. LVD is released after  $t_{VDRELEASE}$  temporization when upper threshold is crossed; LVD is asserted  $t_{VDASSERT}$  after detection when lower threshold is crossed.
2. HVD is released after  $t_{VDRELEASE}$  temporization when lower threshold is crossed; HVD is asserted  $t_{VDASSERT}$  after detection when upper threshold is crossed.
3. POR098\_c threshold is an untrimmed value, before the completion of the power-up sequence. All other LVD/HVD thresholds are provided after trimming.
4. LV internal supply levels are measured on device internal supply grid after internal voltage drop.
5. LV external supply levels are measured on the die side of the package bond wire after package voltage drop.
6.  $V_{DDFLA}$  range is guaranteed when internal flash memory regulator is used.

### 3.11.4 Power sequencing requirements

Requirements for power sequencing include the following.



**Figure 17. Generic input setup/hold timing**

### 3.13.2 Reset and configuration pin timing

**Table 35. Reset and configuration pin timing<sup>1</sup>**

Spec	Characteristic	Symbol	Min	Max	Unit
1	RESET Pulse Width	$t_{RPW}$	10	—	$t_{cyc}$ <sup>2</sup>
2	RESET Glitch Detect Pulse Width	$t_{GPW}$	2	—	$t_{cyc}$ <sup>2</sup>
3	PLLCFG, BOOTCFG, WKPCFG Setup Time to RSTOUT Valid	$t_{RCSU}$	10	—	$t_{cyc}$ <sup>2</sup>
4	PLLCFG, BOOTCFG, WKPCFG Hold Time to RSTOUT Valid	$t_{RCH}$	0	—	$t_{cyc}$ <sup>2</sup>

1. Reset timing specified at:  $V_{DDEH} = 3.0\text{ V to }5.25\text{ V}$ ,  $V_{DD} = 1.08\text{ V to }1.32\text{ V}$ ,  $T_A = T_L\text{ to }T_H$ .

2. For further information on  $t_{cyc}$ , see [Table 3](#).

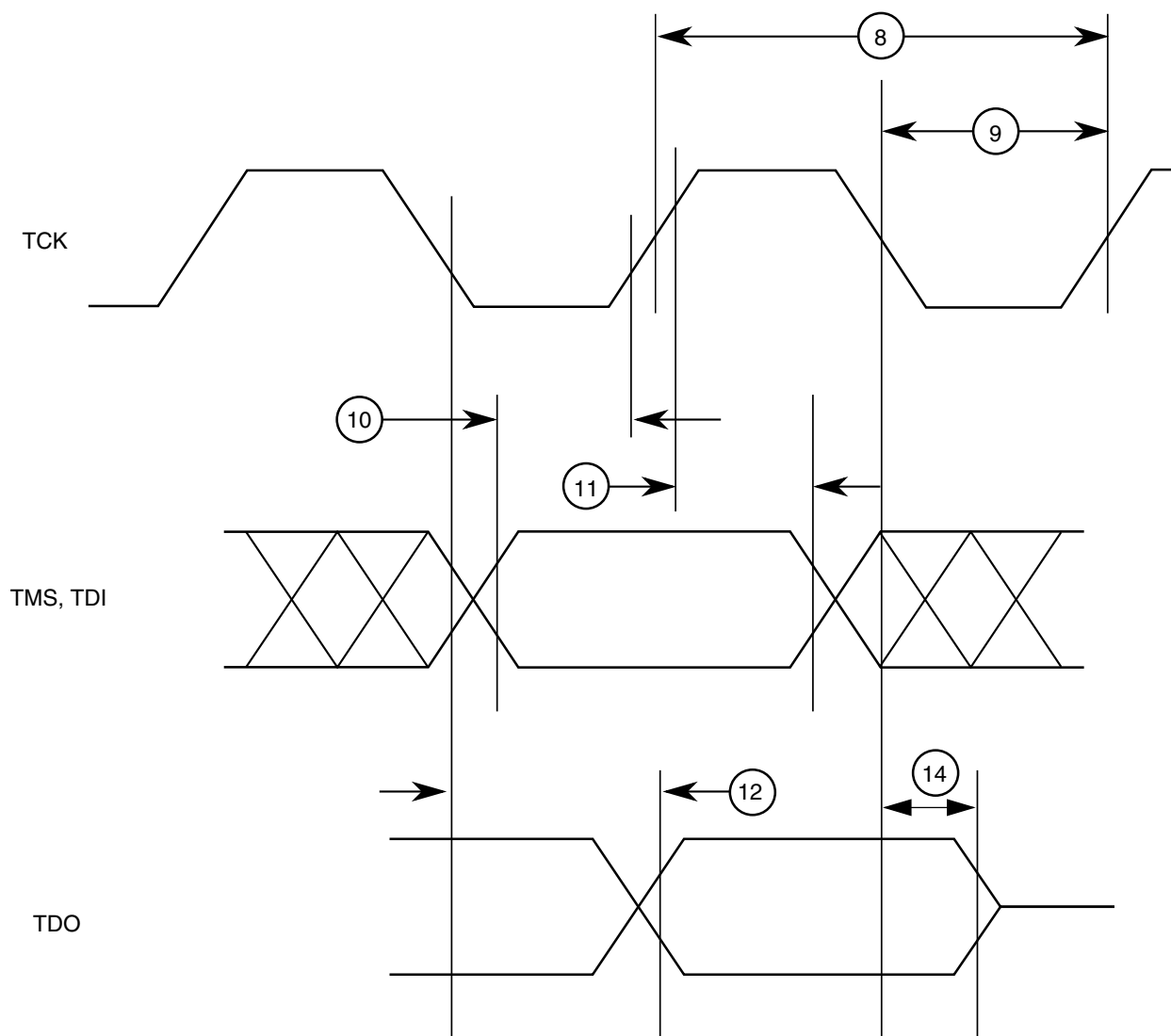


Figure 24. Nexus TCK, TDI, TMS, TDO Timing

### 3.13.5 External Bus Interface (EBI) timing

Table 38. Bus operation timing<sup>1</sup>

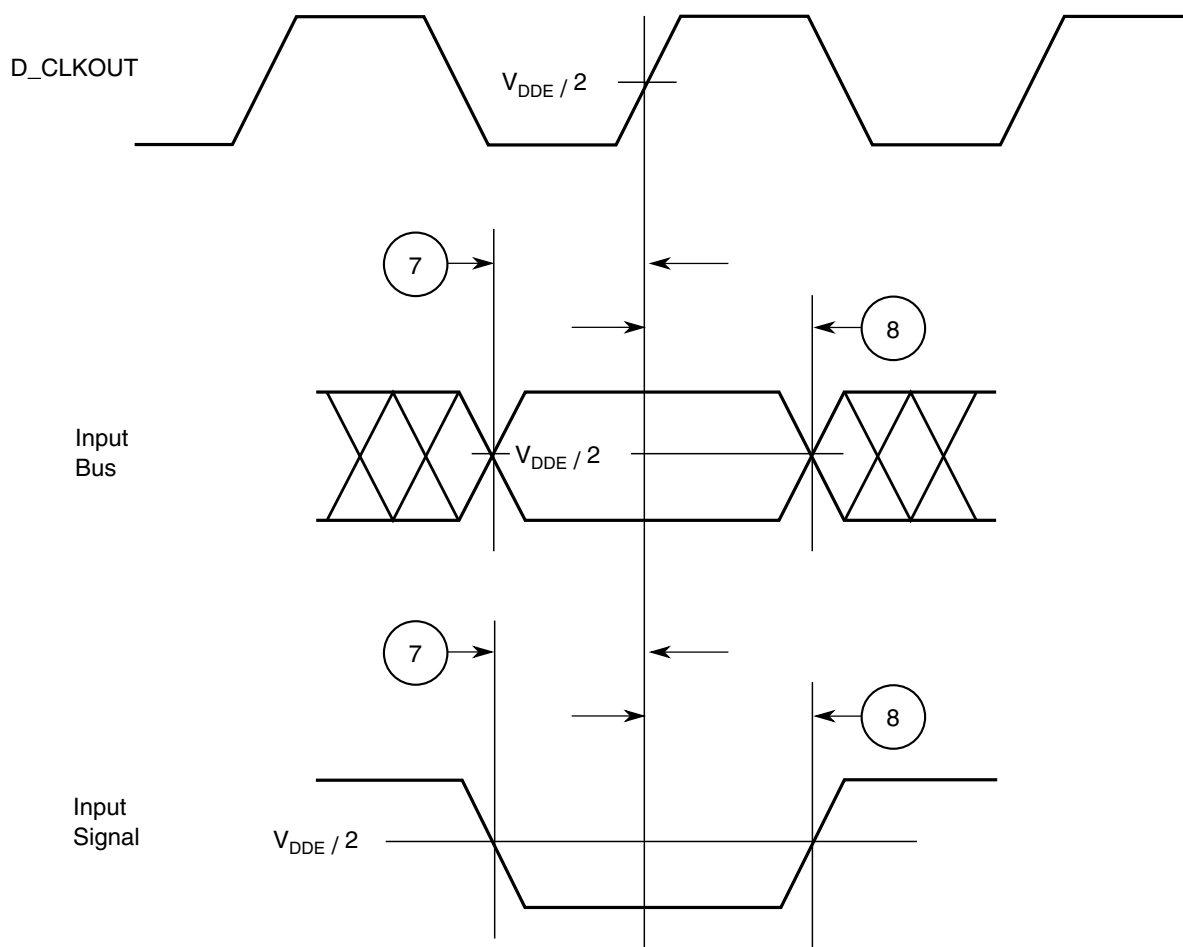
Spec	Characteristic	Symbol	66 MHz (Ext. bus freq.) <sup>2, 3</sup>		Unit	Notes
			Min	Max		
1	D_CLKOUT Period	$t_C$	15.2	—	ns	Signals are measured at 50% $V_{DDE}$ .
2	D_CLKOUT Duty Cycle	$t_{CDC}$	45%	55%	$t_C$	—
3	D_CLKOUT Rise Time	$t_{CRT}$	—	— <sup>4</sup>	ns	—
4	D_CLKOUT Fall Time	$t_{CFT}$	—	— <sup>4</sup>	ns	—

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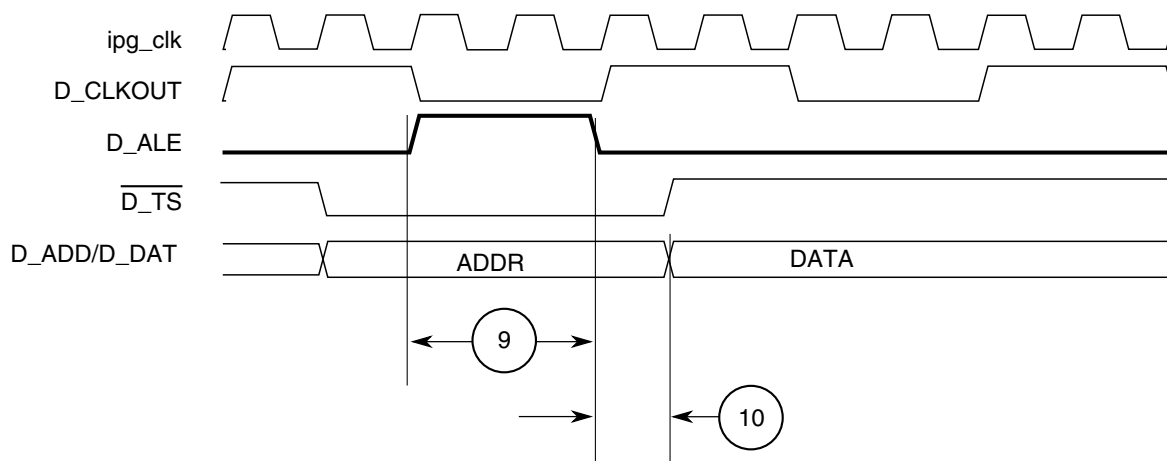
**Table 38. Bus operation timing<sup>1</sup> (continued)**

Spec	Characteristic	Symbol	66 MHz (Ext. bus freq.) <sup>2, 3</sup>		Unit	Notes
			Min	Max		
5	D_CLKOUT Posedge to Output Signal Invalid or High Z (Hold Time) D_ADD[9:30] D_BDIP D_CS[0:3] D_DAT[0:15] D_OE D_RD_WR D_TA D_TS D_WE[0:3]/D_BE[0:3]	t <sub>COH</sub>	1.0/1.5	—	ns	Hold time selectable via SIU_ECCR[EBTS] bit: EBTS = 0: 1.0 ns EBTS = 1: 1.5 ns
6	D_CLKOUT Posedge to Output Signal Valid (Output Delay) D_ADD[9:30] D_BDIP D_CS[0:3] D_DAT[0:15] D_OE D_RD_WR D_TA D_TS D_WE[0:3]/D_BE[0:3]	t <sub>COV</sub>	—	8.5/9.0	ns	Output valid time selectable via SIU_ECCR[EBTS] bit: EBTS = 0: 8.5 ns EBTS = 1: 9.0 ns
				11.5	—	
				8.5/9.0	ns	Output valid time selectable via SIU_ECCR[EBTS] bit: EBTS = 0: 8.5 ns EBTS = 1: 9.0 ns
7	Input Signal Valid to D_CLKOUT Posedge (Setup Time) D_ADD[9:30] D_DAT[0:15] D_RD_WR D_TA D_TS	t <sub>CIS</sub>	7.5	—	ns	—
8	D_CLKOUT Posedge to Input Signal Invalid (Hold Time) D_ADD[9:30] D_DAT[0:15] D_RD_WR D_TA D_TS	t <sub>CIH</sub>	1.0	—	ns	—
9	D_ALE Pulse Width	t <sub>APW</sub>	6.5	—	ns	The timing is for Asynchronous external memory system.

Table continues on the next page...

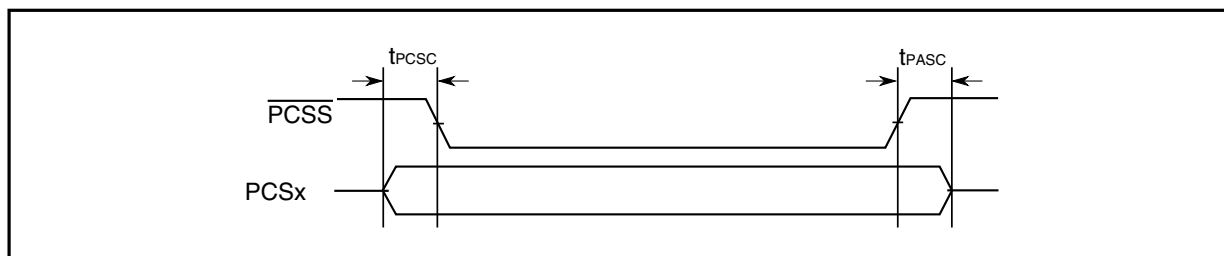


**Figure 27. Synchronous input timing**



**Figure 28. ALE signal timing**



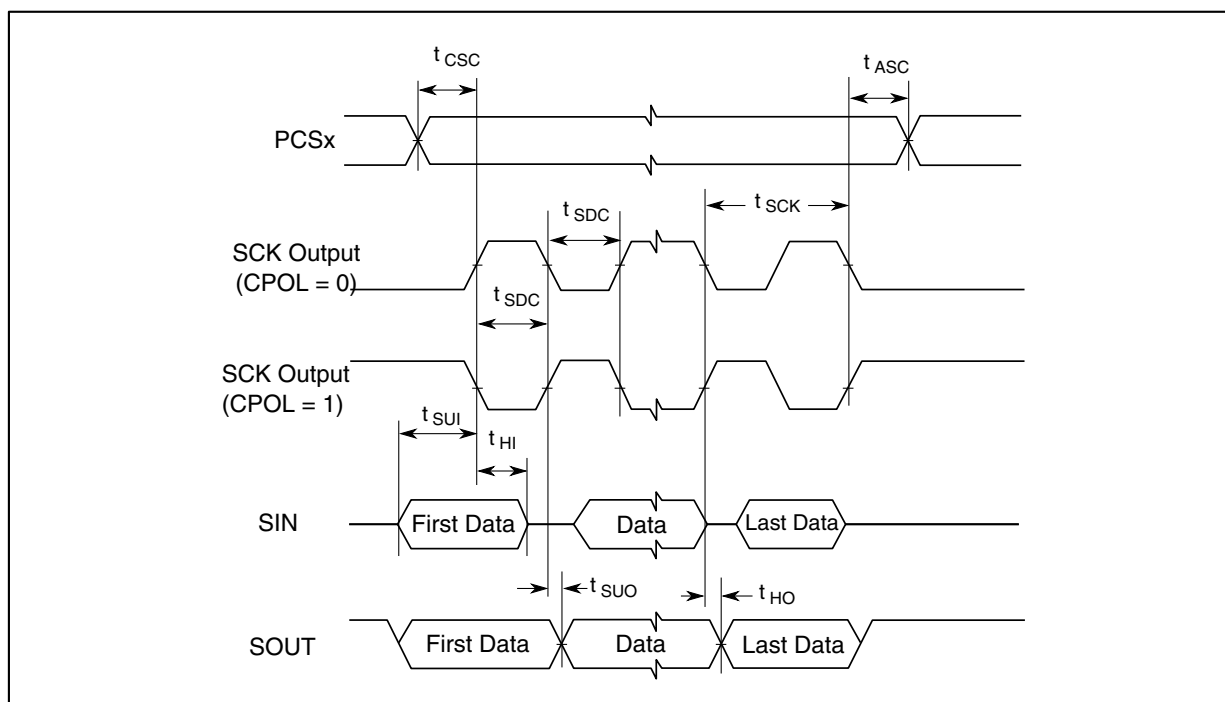
Figure 37. DSPI PCS strobe ( $\overline{\text{PCSS}}$ ) timing (master mode)

## 3.13.9.1.3 DSPI LVDS Master Mode – Modified Timing

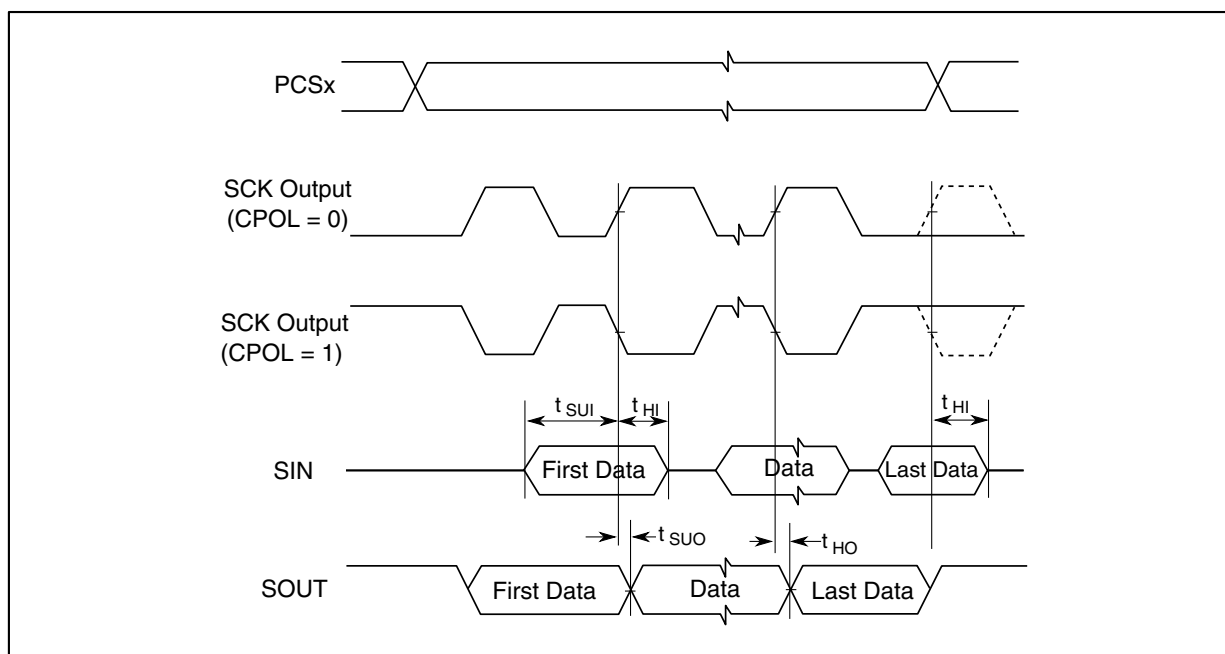
Table 45. DSPI LVDS master timing – full duplex – modified transfer format (MTFE = 1), CPHA = 0 or 1

#	Symbol	Characteristic	Condition <sup>1</sup>		Value <sup>2</sup>		Unit
			Pad drive <sup>3</sup>	Load (C <sub>L</sub> )	Min	Max	
1	t <sub>SCK</sub>	SCK cycle time	LVDS	15 pF to 25 pF differential	33.3	—	ns
2	t <sub>CSC</sub>	PCS to SCK delay (LVDS SCK)	PCS: PCR[SRC]=11b	25 pF	(N <sup>4</sup> × t <sub>SYS</sub> <sup>5</sup> ) – 10	—	ns
			PCS: PCR[SRC]=10b	50 pF	(N <sup>4</sup> × t <sub>SYS</sub> <sup>5</sup> ) – 10	—	ns
			PCS: PCR[SRC]=01b	50 pF	(N <sup>4</sup> × t <sub>SYS</sub> <sup>5</sup> ) – 32	—	ns
3	t <sub>ASC</sub>	After SCK delay (LVDS SCK)	PCS: PCR[SRC]=11b	PCS: 0 pF SCK: 25 pF	(M <sup>6</sup> × t <sub>SYS</sub> <sup>5</sup> ) – 8	—	ns
			PCS: PCR[SRC]=10b	PCS: 0 pF SCK: 25 pF	(M <sup>6</sup> × t <sub>SYS</sub> <sup>5</sup> ) – 8	—	ns
			PCS: PCR[SRC]=01b	PCS: 0 pF SCK: 25 pF	(M <sup>6</sup> × t <sub>SYS</sub> <sup>5</sup> ) – 8	—	ns
4	t <sub>SDC</sub>	SCK duty cycle <sup>7</sup>	LVDS	15 pF to 25 pF differential	1/2t <sub>SCK</sub> – 2	1/2t <sub>SCK</sub> + 2	ns
7	t <sub>SUI</sub>	SIN setup time					
		SIN setup time to SCK CPHA = 0 <sup>8</sup>	LVDS	15 pF to 25 pF differential	23 – (P <sup>9</sup> × t <sub>SYS</sub> <sup>5</sup> )	—	ns
		SIN setup time to SCK CPHA = 1 <sup>8</sup>	LVDS	15 pF to 25 pF differential	23	—	ns
8	t <sub>HI</sub>	SIN hold time					
		SIN hold time from SCK CPHA = 0 <sup>8</sup>	LVDS	0 pF differential	–1 + (P <sup>9</sup> × t <sub>SYS</sub> <sup>5</sup> )	—	ns
		SIN hold time from SCK CPHA = 1 <sup>8</sup>	LVDS	0 pF differential	–1	—	ns

Table continues on the next page...



**Figure 38. DSPI LVDS master mode – modified timing, CPHA = 0**



**Figure 39. DSPI LVDS master mode – modified timing, CPHA = 1**

## Package information

- Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

**Table 55. Thermal characteristics, 516-ball MAPBGA package**

Characteristic	Symbol	Value	Unit
Junction to Ambient <sup>1,2</sup> Natural Convection (Single layer board)	$R_{\Theta JA}$	28.5	°C/W
Junction to Ambient <sup>1,3</sup> Natural Convection (Four layer board 2s2p)	$R_{\Theta JA}$	20.0	°C/W
Junction to Ambient (@200 ft./min., Single layer board)	$R_{\Theta JMA}$	21.3	°C/W
Junction to Ambient (@200 ft./min., Four layer board 2s2p)	$R_{\Theta JMA}$	15.5	°C/W
Junction to Board <sup>4</sup>	$R_{\Theta JB}$	8.8	°C/W
Junction to Case <sup>5</sup>	$R_{\Theta JC}$	4.8	°C/W
Junction to Package Top <sup>6</sup> Natural Convection	$\Psi_{JT}$	0.2	°C/W

- Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
- Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
- Per JEDEC JESD51-6 with the board horizontal.
- Thermal resistance between the die and the printed circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
- Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature.
- Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2.

### 4.1.1 General notes for thermal characteristics

An estimation of the chip junction temperature,  $T_J$ , can be obtained from the equation:

$$T_J = T_A + (R_{\Theta JA} * P_D)$$

where:

$T_A$  = ambient temperature for the package (°C)

$R_{\Theta JA}$  = junction-to-ambient thermal resistance (°C/W)

$P_D$  = power dissipation in the package (W)

The thermal resistance values used are based on the JEDEC JESD51 series of standards to provide consistent values for estimations and comparisons. The difference between the values determined for the single-layer (1s) board compared to a four-layer board that has two signal layers, a power and a ground plane (2s2p), demonstrate that the effective thermal resistance is not a constant. The thermal resistance depends on the:

- Construction of the application board (number of planes)
- Effective size of the board which cools the component

1 mm of wire extending from the junction. Place the thermocouple wire flat against the package case to avoid measurement errors caused by the cooling effects of the thermocouple wire.

When board temperature is perfectly defined below the device, it is possible to use the thermal characterization parameter ( $\Psi_{JPB}$ ) to determine the junction temperature by measuring the temperature at the bottom center of the package case (exposed pad) using the following equation:

$$T_J = T_B + (\Psi_{JPB} \times P_D)$$

where:

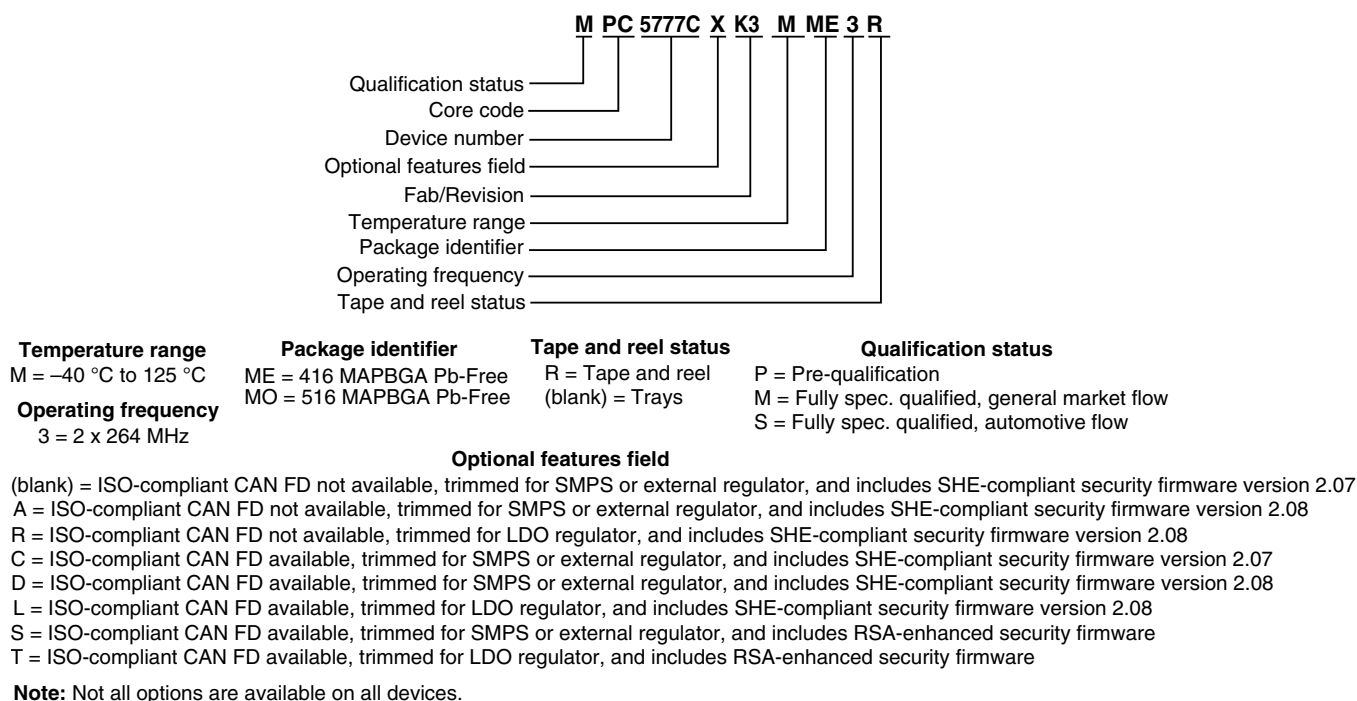
$T_T$  = thermocouple temperature on bottom of the package ( $^{\circ}\text{C}$ )

$\Psi_{JT}$  = thermal characterization parameter ( $^{\circ}\text{C}/\text{W}$ )

$P_D$  = power dissipation in the package (W)

## 5 Ordering information

Figure 47 and Table 56 describe orderable part numbers for the MPC5777C.



**Figure 47. MPC5777C Orderable part number description**

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Document Number MPC5777C  
Revision 11, 04/2017

